Technical Data Data Sheet 4958, Rev.-

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop (150 °C T_J Operation)

Applications:

Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	1	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	20	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25 \ ^{\circ}C, \ I_{AS} = 0.74 \ A, L = 18 \ mH$	5.0	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 µs f limited by T _J max V _A =1.5V _R	0.74	A
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T_{stg}	-	-65 to +150	°C

Electrical Characteristics⁽¹⁾:

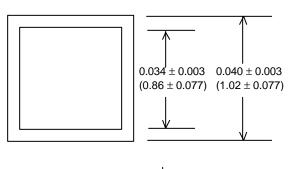
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 1A, Pulse, T _J = 25 °C	0.56	V
	V _{F2}	@ 1A, Pulse, T _J = 125 °C	0.51	V
Max. Reverse Current	I _{R1}	$@V_{R} = 45V$, Pulse,	100	μA
		$T_J = 25 \ ^{\circ}C$		
	I _{R2}	$@V_R = 45V$, Pulse,	4.5	mA
		T _J = 125 °C		
Max. Junction Capacitance	CT	$@V_{R} = 5V, T_{C} = 25 \ ^{\circ}C$	53	pF
		f _{SIG} = 1MHz,		
		$V_{SIG} = 50 \text{mV} (\text{p-p})$		

(1) in SHD package

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Technical Data Data Sheet 4958, Rev.-

Mechanical Dimensions: In Inches / mm

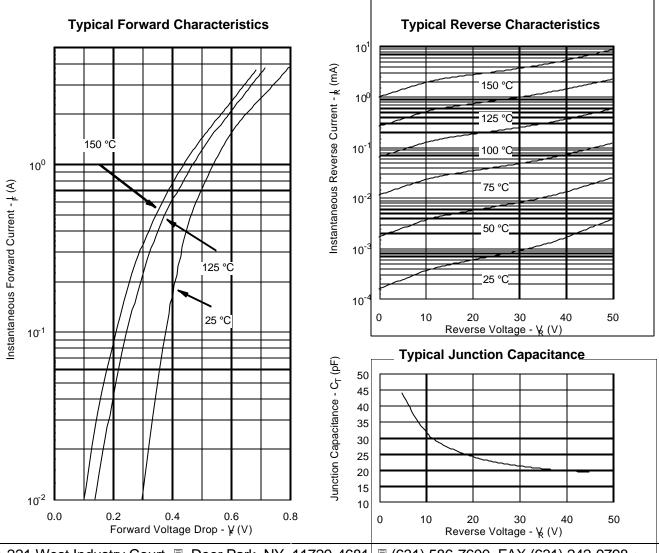


Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization AI - 25 kÅ minimum or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

Dimension H = 0.0105 ± 0.001 (0.27 ± 0.026) for Al top; Dimension H = 0.0155 ± 0.001 (0.39 ± 0.026) for Ag top.





TECHNICAL DATA

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